

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	I_D $T_A = 25^\circ\text{C}$
-25V	26m Ω @ $V_{GS} = -4.5\text{V}$	-7.3
	40m Ω @ $V_{GS} = -1.8\text{V}$	-6.0

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

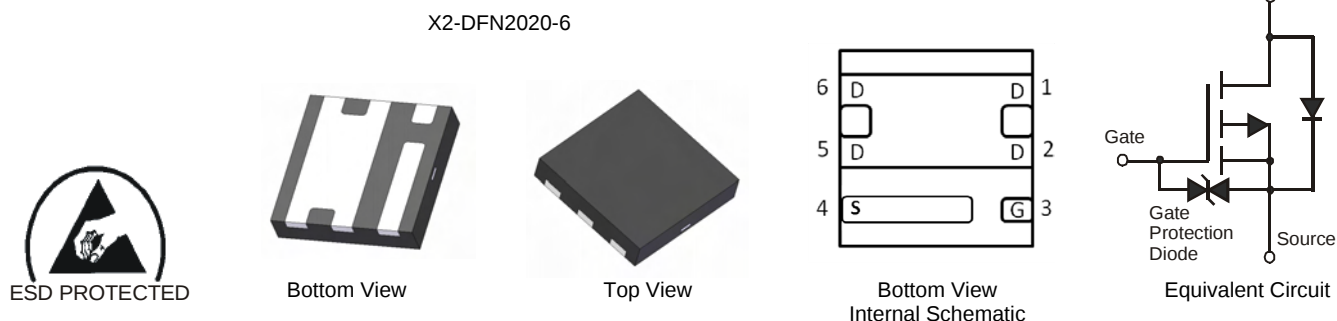
- Load Switching
- Battery Management Application
- Power Management Functions

Features and Benefits

- Low $R_{DS(on)}$ – ensures on state losses are minimized
- 0.4mm profile – ideal for low profile applications
- PCB footprint of 4mm²
- Low Input Capacitance
- **ESD Protected Gate**
- **Lead, Halogen, and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X2-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

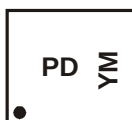


Ordering Information (Note 3)

Part Number	Case	Packaging
DMP2039UFDE4-7	X2-DFN2020-6	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



PD = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)
 Dot Denotes Pin 1

Date Code Key

Year Code	2011	2012	2013	2014	2015	2016	2017
	Y	Z	A	B	C	D	E

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-25	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = 25°C T _A = 70°C	I _D	-7.3 -5.8	A
	t < 5s	T _A = 25°C T _A = 70°C	I _D	-9.2 -7.3	A
Continuous Drain Current (Note 5) V _{GS} = -1.8V	Steady State	T _A = 25°C T _A = 70°C	I _D	-6.0 -4.7	A
	t < 5s	T _A = 25°C T _A = 70°C	I _D	-7.6 -6.0	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	-60	A
Continuous Source-Drain Diode Current			I _S	-2.0	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 4)	T _A = 25°C	P _D	0.69	W
	T _A = 70°C		0.44	
Thermal Resistance, Junction to Ambient (Note 4)	Steady state	R _{θJA}	182	°C/W
	t < 5s		113	
Total Power Dissipation (Note 5)	T _A = 25°C	P _D	2.4	W
	T _A = 70°C		1.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	52	°C/W
	t < 5s		33	
Thermal Resistance, Junction to Case (Note 5)	Steady state	R _{θJC}	9.1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-25	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -25V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±8.0V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	19	26	mΩ	V _{GS} = -4.5V, I _D = -6.4A
		—	24	33		V _{GS} = -2.5V, I _D = -4.8A
		—	29	40		V _{GS} = -1.8V, I _D = -2.5A
		—	35	70		V _{GS} = -1.5V, I _D = -1.5A
		—	—	—		V _{GS} = -1.5V, I _D = -1.5A
Forward Transfer Admittance	Y _{fs}	—	14	—	mS	V _{DS} = -5V, I _D = -4A
Diode Forward Voltage (Note 5)	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	2530	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	203	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	177	—	pF	
Gate Resistance	R _g	—	9.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	28.2	—	nC	V _{DS} = -15V, I _D = -4.0A
Gate-Source Charge	Q _{gs}	—	48.7	—		
Gate-Drain Charge	Q _{gd}	—	3.2	—		
Turn-On Delay Time	t _{D(on)}	—	5.0	—	nS	V _{DD} = -15V, V _{GS} = -4.5V, R _G = 1Ω, I _D = -4.0A
Turn-On Rise Time	t _r	—	15.1	—		
Turn-Off Delay Time	t _{D(off)}	—	23.5	—		
Turn-Off Fall Time	t _f	—	137.6	—		

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
 - Short duration pulse test used to minimize self-heating effect
 - Guaranteed by design. Not subject to production testing.

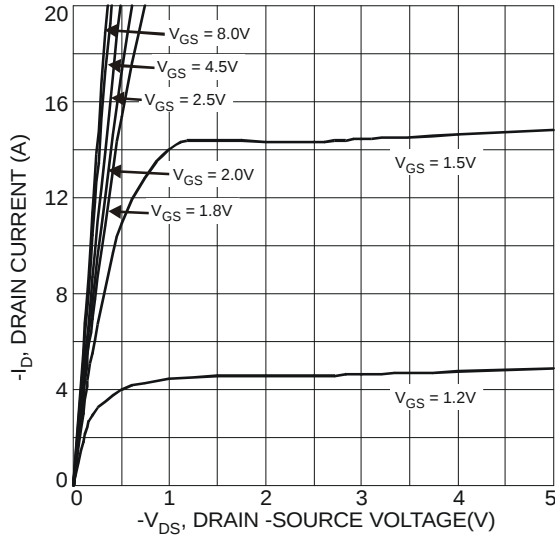


Fig. 1 Typical Output Characteristics

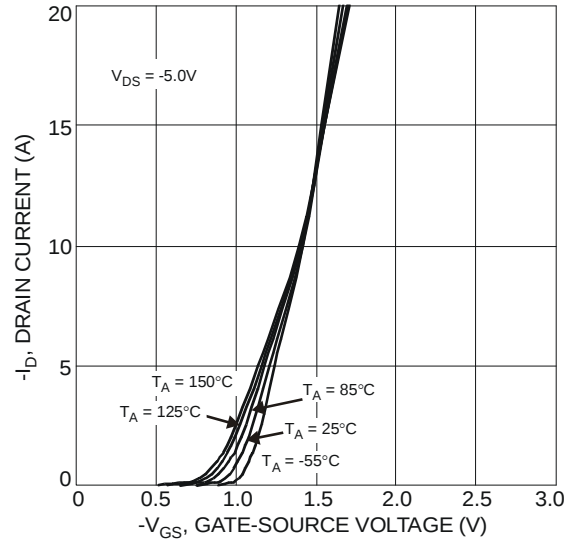


Fig. 2 Typical Transfer Characteristics

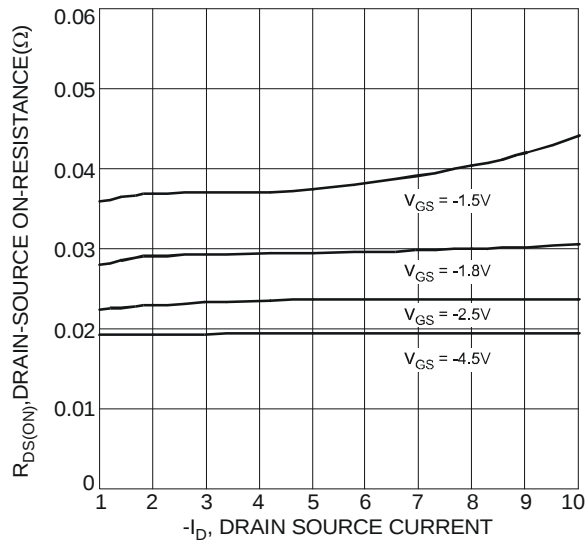


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

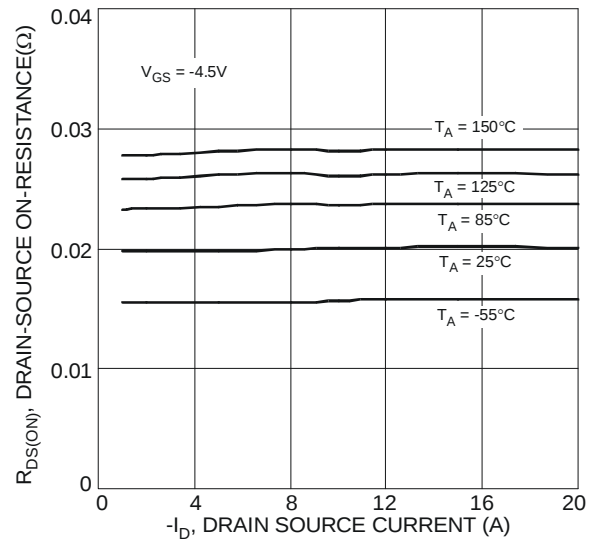


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

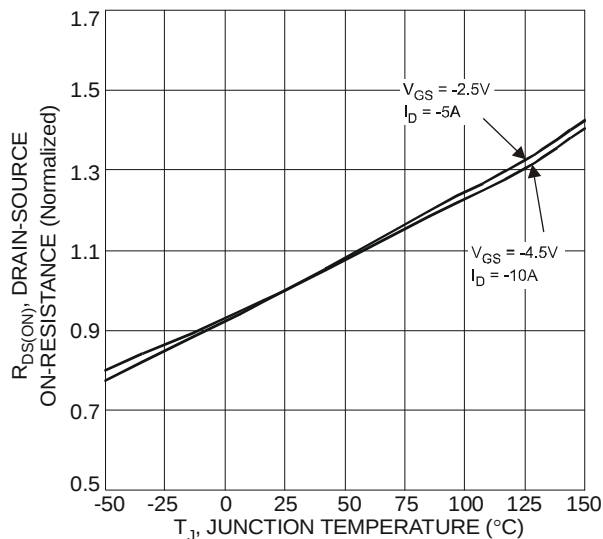


Fig. 5 On-Resistance Variation with Temperature

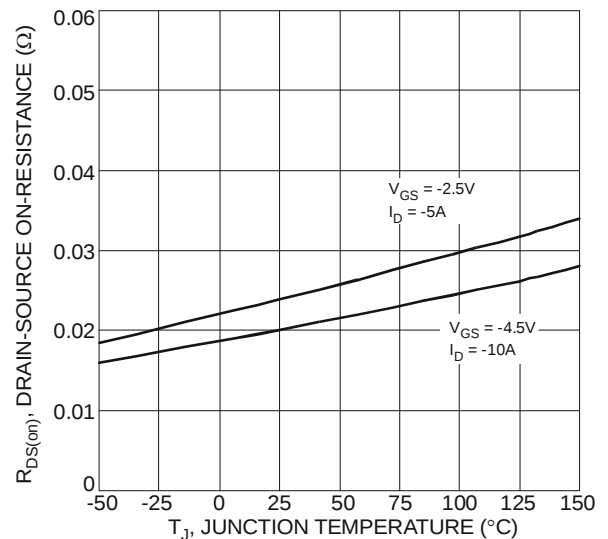


Fig. 6 On-Resistance Variation with Temperature

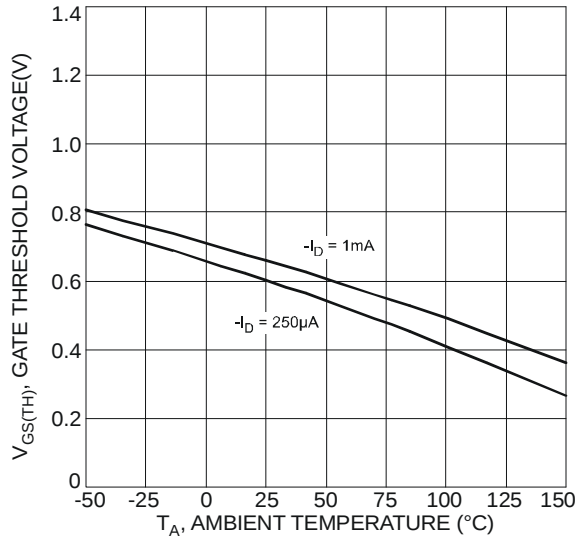


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

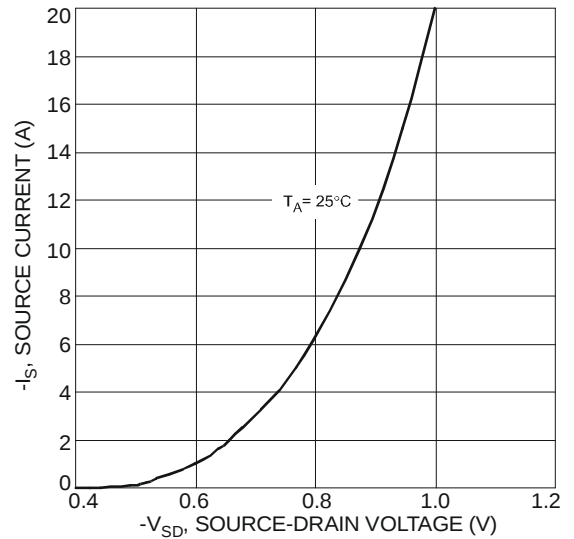


Fig. 8 Diode Forward Voltage vs. Current

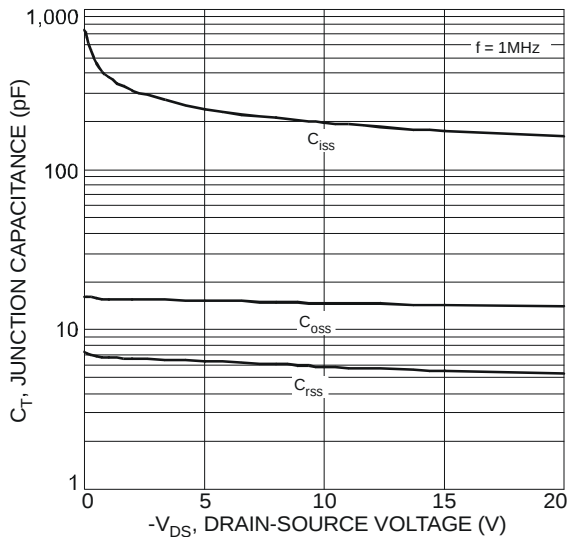


Fig. 9 Typical Junction Capacitance

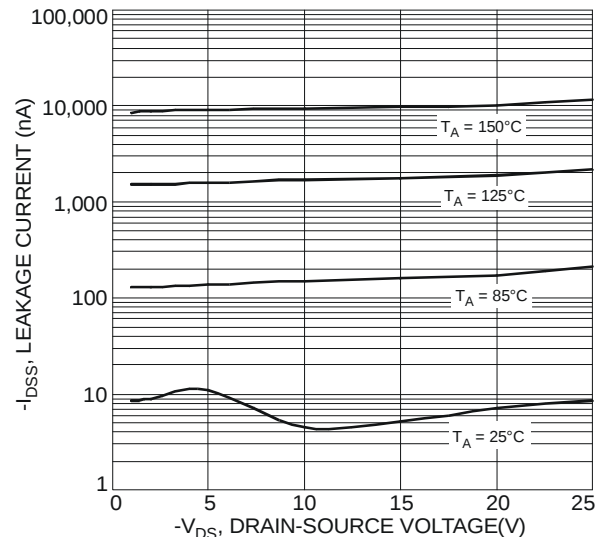


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

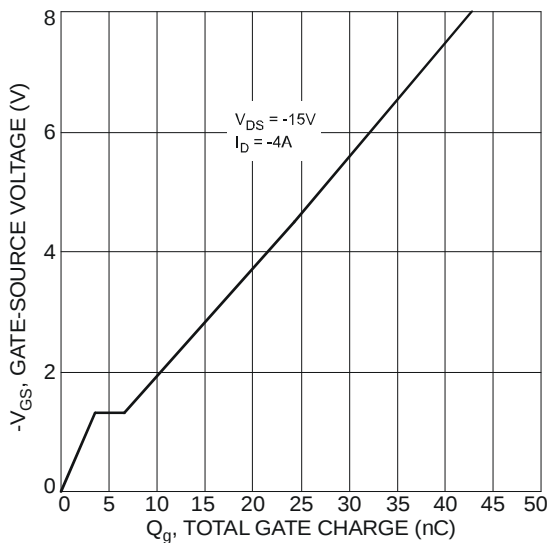


Fig. 11 Gate-Charge Characteristics

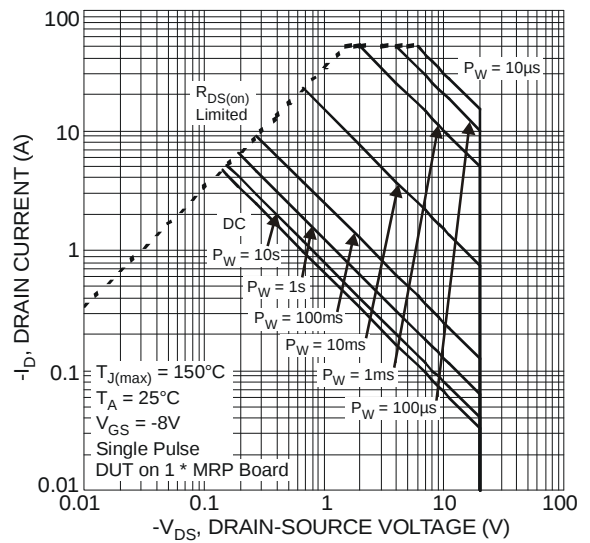
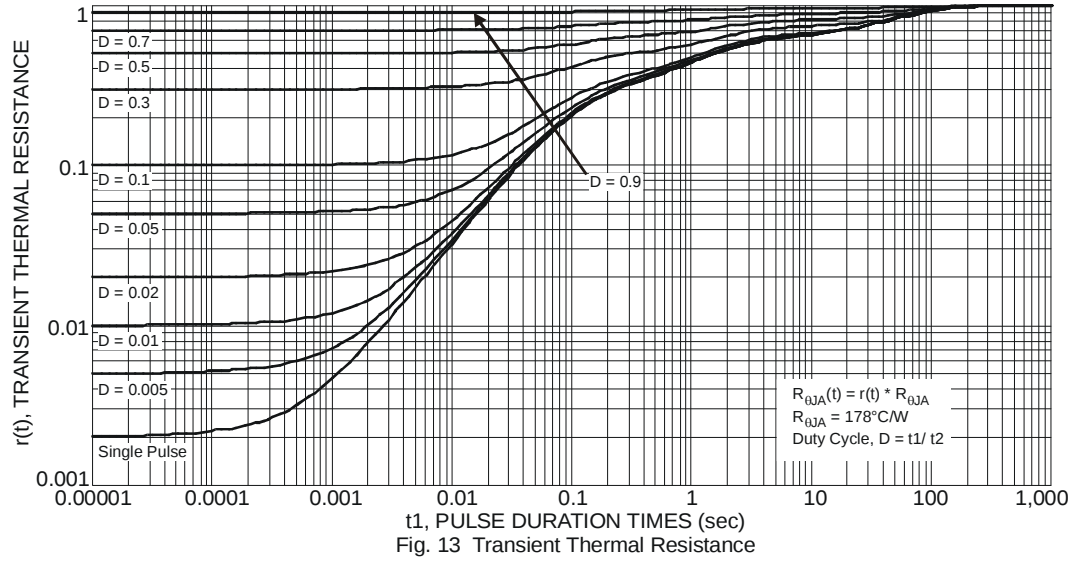
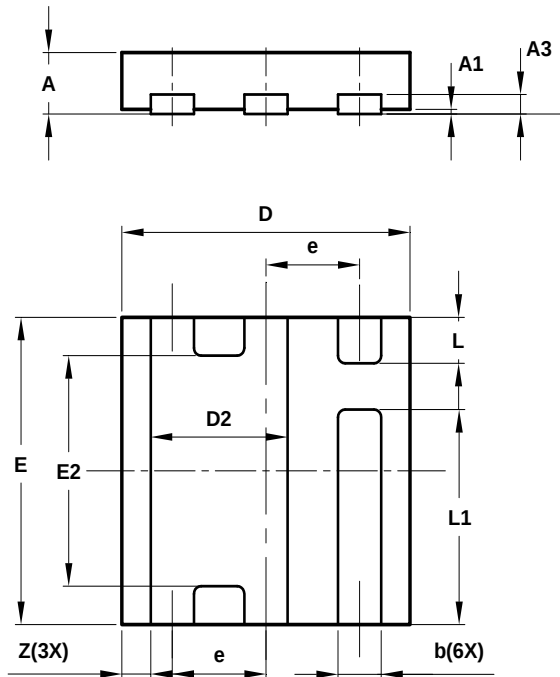


Fig. 12 SOA, Safe Operation Area

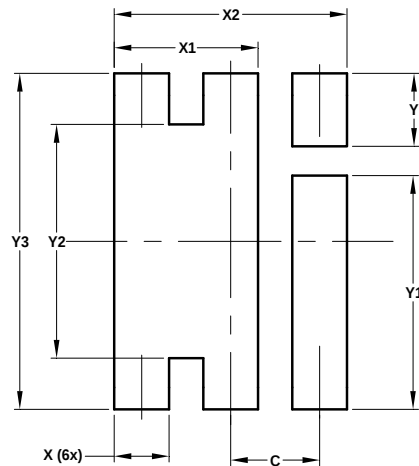


Package Outline Dimensions



X2-DFN2020-6			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.03
A3	—	—	0.13
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	1.35	1.45	1.40
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	1.050
X2	1.700
Y	0.500
Y1	1.600
Y2	1.600
Y3	2.300

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